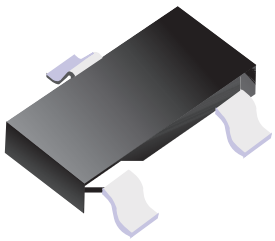
For switching and general purpose applications.

The transistor is subdivided into three groups O, Y and G, according to its DC current gain.

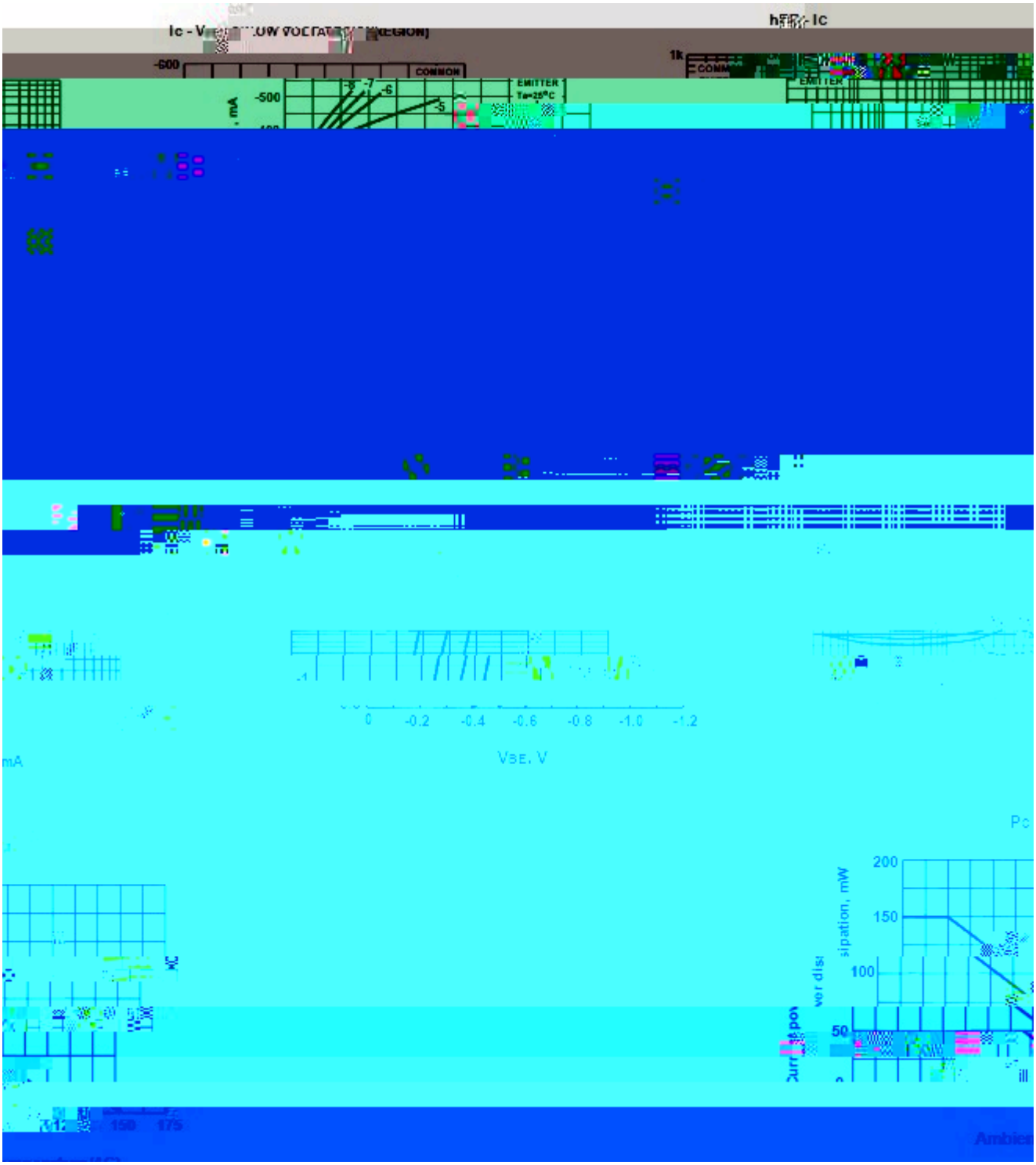


- Excellent h_{FE} linearity:
- h_{FE}=25(min) at V_{CE}=-6V, I_C=-400mA

Collector-Base Voltage		-35	
Collector-Emitter Voltage		-30	
Emitter -Base Voltage		-5	
Collector Current-Continuous		-500	
Base Current		-50	
Power Dissipation		200	
Junction Temperature		150	
Storage Temperature		-55-+150	

DC Current Gain	V_{CE}=-1V,I_C= -100mA	O	70		140
		Y	120		240
Current Gain Group		G	200		400
Collector Cutof	V_{CE}=-6V,I_C= -400mA			25	

	70-140	120-240	200-400
	AZO	AZY	AZG


-600
COMMON
EMITTER
Ta=25°C
-500
mA
-8
-7
-6
-5
1k
EMITTER
0
-0.2
-0.4
-0.6
-0.8
-1.0
-1.2
VBE, V
mA
200
150
100
50
150
175

Ordering information

Package	Packing Description	Base Quantity	Packing Quantity
SOT-23	Tape/Reel,7”reel	3000pcs/Reel	24000PCS/Box 120000PCS/Carton

Package Dimensions

SOT-23

Dim.	Millimeter (mm)		mil	
	Min.	**Max.**	**Min.**	**Max.**
A	0.9	1.15	35	45
A1	0.1		3.9	
bp	0.38	0.48	15	19
C	0.09	0.15	3.54	5.9
D	2.8	3.0	110	118

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed